

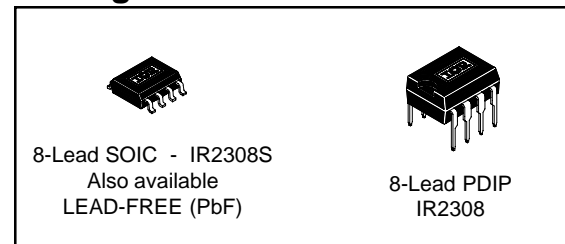
## IR2308(S) & (PbF)

### HALF-BRIDGE DRIVER

#### Features

- Floating channel designed for bootstrap operation  
 Fully operational to +600V  
 Tolerant to negative transient voltage  
 dV/dt immune
- Gate drive supply range from 10 to 20V
- Undervoltage lockout for both channels
- 3.3V, 5V and 15V input logic compatible
- Cross-conduction prevention logic
- Matched propagation delay for both channels
- Outputs in phase with inputs
- Logic and power ground +/- 5V offset.
- Internal 540ns dead-time
- Lower di/dt gate driver for better noise immunity
- Also available LEAD\_FREE

#### Packages



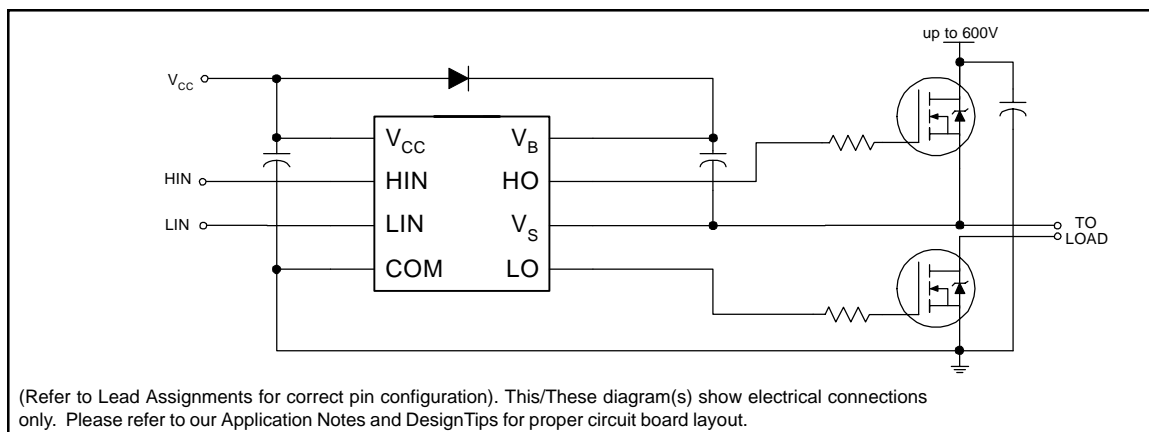
#### 2106//2108//2109/2304/2308 Feature Comparison

Part	Input logic	Cross-conduction prevention logic	Dead-Time	Ground Pins
2106	HIN/LIN	no	none	COM
21064				VSS/COM
2108	HIN/LIN	yes	Internal 540ns Programmable 0.54-5 μs	COM
21084				VSS/COM
2109	IN/SD	yes	Internal 540ns Programmable 0.54-5 μs	COM
21094				VSS/COM
2304	HIN/LIN	yes	Internal 100ns	COM
2308	HIN/LIN	yes	Internal 540ns	COM

#### Description

The IR2308(S) are high voltage, high speed power MOSFET and IGBT drivers with dependent high and low side referenced output channels. Proprietary HVIC and latch immune CMOS technologies enable ruggedized monolithic construction. The logic input is compatible with standard CMOS or LSTTL output, down to 3.3V logic. The output drivers feature a high pulse current buffer stage designed for minimum driver cross-conduction. The floating channel can be used to drive an N-channel power MOSFET or IGBT in the high side configuration which operates up to 600 volts.

#### Typical Connection



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## Absolute Maximum Ratings

Absolute maximum ratings indicate sustained limits beyond which damage to the device may occur. All voltage parameters are absolute voltages referenced to COM. The thermal resistance and power dissipation ratings are measured under board mounted and still air conditions.

Symbol	Definition	Min.	Max.	Units	
V <sub>B</sub>	High side floating absolute voltage	-0.3	625	V	
V <sub>S</sub>	High side floating supply offset voltage	V <sub>B</sub> - 25	V <sub>B</sub> + 0.3		
V <sub>HO</sub>	High side floating output voltage	V <sub>S</sub> - 0.3	V <sub>B</sub> + 0.3		
V <sub>CC</sub>	Low side and logic fixed supply voltage	-0.3	25		
V <sub>LO</sub>	Low side output voltage	-0.3	V <sub>CC</sub> + 0.3		
V <sub>IN</sub>	Logic input voltage (HIN & LIN )	V <sub>SS</sub> - 0.3	V <sub>CC</sub> + 0.3		
dV <sub>S</sub> /dt	Allowable offset supply voltage transient	—	50	V/ns	
P <sub>D</sub>	Package power dissipation @ T <sub>A</sub> ≤ +25°C	(8 lead PDIP)	—	1.0	W
		(8 lead SOIC)	—	0.625	
R <sub>thJA</sub>	Thermal resistance, junction to ambient	(8 lead PDIP)	—	125	°C/W
		(8 lead SOIC)	—	200	
T <sub>J</sub>	Junction temperature	—	150	°C	
T <sub>S</sub>	Storage temperature	-50	150		
T <sub>L</sub>	Lead temperature (soldering, 10 seconds)	—	300		

## Recommended Operating Conditions

The Input/Output logic timing diagram is shown in figure 1. For proper operation the device should be used within the recommended conditions. The V<sub>S</sub> and V<sub>SS</sub> offset rating are tested with all supplies biased at 15V differential.

Symbol	Definition	Min.	Max.	Units
V <sub>B</sub>	High side floating supply absolute voltage	V <sub>S</sub> + 10	V <sub>S</sub> + 20	V
V <sub>S</sub>	High side floating supply offset voltage	Note 1	600	
V <sub>HO</sub>	High side floating output voltage	V <sub>S</sub>	V <sub>B</sub>	
V <sub>CC</sub>	Low side and logic fixed supply voltage	10	20	
V <sub>LO</sub>	Low side output voltage	0	V <sub>CC</sub>	
V <sub>IN</sub>	Logic input voltage	COM	V <sub>CC</sub>	
T <sub>A</sub>	Ambient temperature	-40	125	°C

Note 1: Logic operational for V<sub>S</sub> of -5 to +600V. Logic state held for V<sub>S</sub> of -5V to -V<sub>BS</sub>. (Please refer to the Design Tin DT97-3 for more details).

## Dynamic Electrical Characteristics

$V_{BIAS}$  ( $V_{CC}$ ,  $V_{BS}$ ) = 15V,  $V_{SS}$  = COM,  $C_L$  = 1000 pF,  $T_A$  = 25°C, DT =  $V_{SS}$  unless otherwise specified.

Symbol	Definition	Min.	Typ.	Max.	Units	Test Conditions
$t_{on}$	Turn-on propagation delay	—	220	300	nsec	$V_S = 0V$
$t_{off}$	Turn-off propagation delay	—	200	280		$V_S = 0V$ or $600V$
MT	Delay matching $ t_{on} - t_{off} $	—	0	46		
$t_r$	Turn-on rise time	—	150	220		$V_S = 0V$
$t_f$	Turn-off fall time	—	50	80		$V_S = 0V$
DT	Deadtime: LO turn-off to HO turn-on(DT <sub>LO-HO</sub> ) & HO turn-off to LO turn-on (DT <sub>HO-LO</sub> )	400	540	680		
MDT	Deadtime matching = $ DT_{LO-HO} - DT_{HO-LO} $	—	0	60		

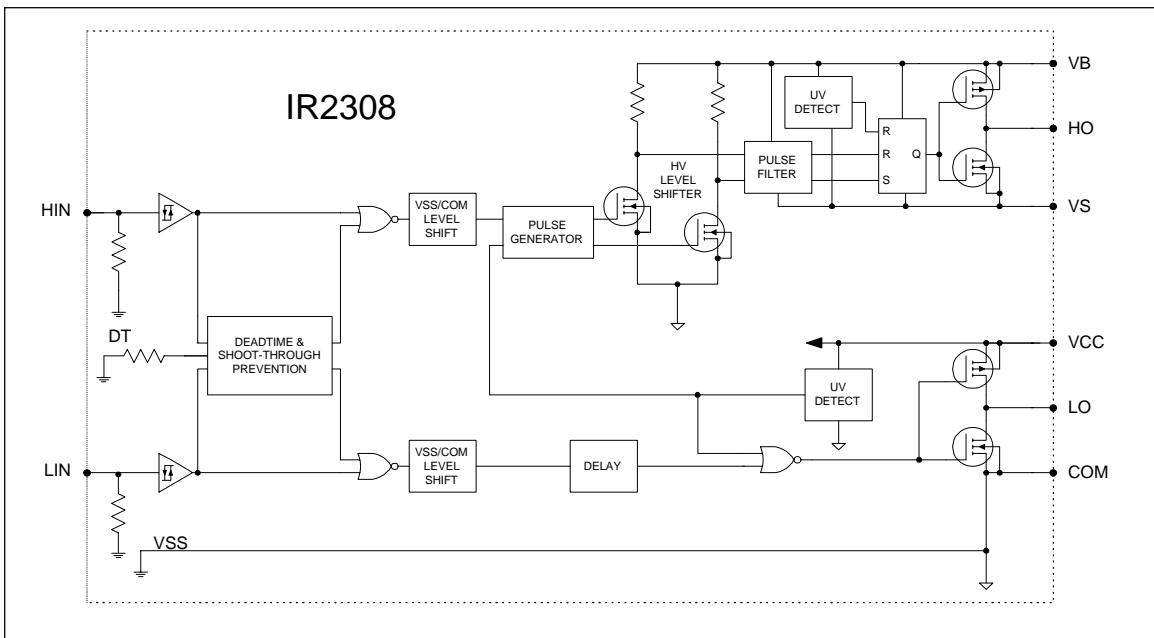
## Static Electrical Characteristics

$V_{BIAS}$  ( $V_{CC}$ ,  $V_{BS}$ ) = 15V,  $V_{SS}$  = COM, DT =  $V_{SS}$  and  $T_A$  = 25°C unless otherwise specified. The  $V_{IL}$ ,  $V_{IH}$  and  $I_{IN}$  parameters are referenced to  $V_{SS}/COM$  and are applicable to the respective input leads: HIN and LIN. The  $V_O$ ,  $I_O$  and  $R_{on}$  parameters are referenced to COM and are applicable to the respective output leads: HO and LO.

Symbol	Definition	Min.	Typ.	Max.	Units	Test Conditions
$V_{IH}$	Logic "1" input voltage for HIN & LIN	2.9	—	—	V	$V_{CC} = 10V$ to $20V$
$V_{IL}$	Logic "0" input voltage for HIN & LIN	—	—	0.8		$V_{CC} = 10V$ to $20V$
$V_{OH}$	High level output voltage, $V_{BIAS} - V_O$	—	0.8	1.4		$I_O = 20$ mA
$V_{OL}$	Low level output voltage, $V_O$	—	0.3	0.6		$I_O = 20$ mA
$I_{LK}$	Offset supply leakage current	—	—	50	$\mu A$	$V_B = V_S = 600V$
$I_{QBS}$	Quiescent $V_{BS}$ supply current	20	60	150	$\mu A$	$V_{IN} = 0V$ or $5V$
$I_{QCC}$	Quiescent $V_{CC}$ supply current	0.4	1.0	1.6	mA	$V_{IN} = 0V$ or $5V$
$I_{IN+}$	Logic "1" input bias current	—	5	20	$\mu A$	HIN = 5V, LIN = 5V
$I_{IN-}$	Logic "0" input bias current	—	1	2		HIN = 0V, LIN = 0V
$V_{CCUV+}$ $V_{BSUV+}$	$V_{CC}$ and $V_{BS}$ supply undervoltage positive going threshold	8.0	8.9	10	V	
$V_{CCUV-}$ $V_{BSUV-}$	$V_{CC}$ and $V_{BS}$ supply undervoltage negative going threshold	7.4	8.2	9.0		
$V_{CCUVH}$ $V_{BSUVH}$	Hysteresis	0.3	0.7	—		
$I_{O+}$	Output high short circuit pulsed current	97	200	—	mA	$V_O = 0V$ , PW $\leq 10$ $\mu s$
$I_{O-}$	Output low short circuit pulsed current	250	350	—		$V_O = 15V$ , PW $\leq 10$ $\mu s$

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## Functional Block Diagram



## Lead Definitions

Symbol	Description
HIN	Logic input for high side gate driver output (HO), in phase
LIN	Logic input for low side gate driver output (LO), in phase
V <sub>B</sub>	High side floating supply
HO	High side gate driver output
V <sub>S</sub>	High side floating supply return
V <sub>CC</sub>	Low side and logic fixed supply
LO	Low side gate driver output
COM	Low side return

## Lead Assignments

<p>8 Lead PDIP</p>	<p>8 Lead SOIC            Also available LEAD-FREE(PbF)</p>
<b>IR2308</b>	<b>IR2308S</b>

# IR2308(S) & (PbF)

International  
**IR** Rectifier

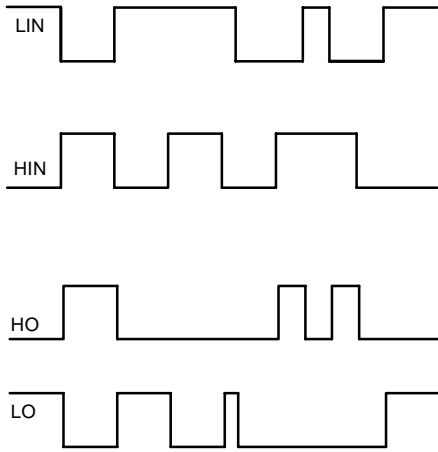


Figure 1. Input/Output Timing Diagram

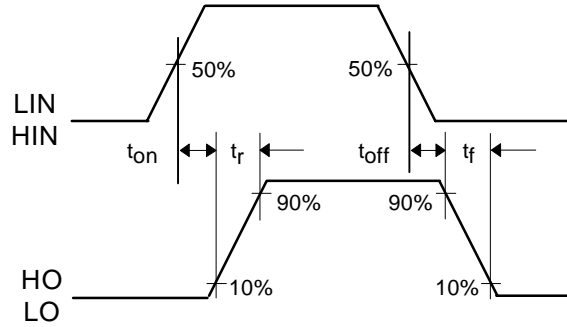


Figure 2. Switching Time Waveform Definitions

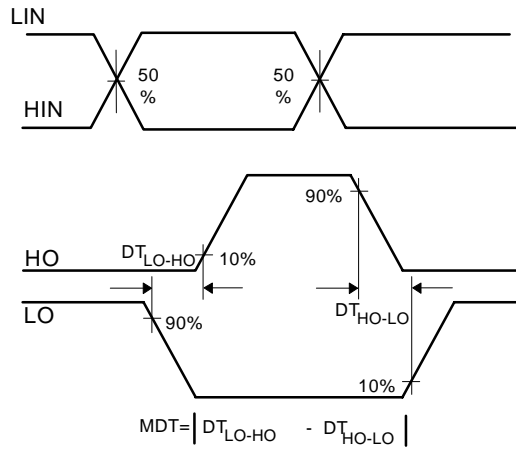
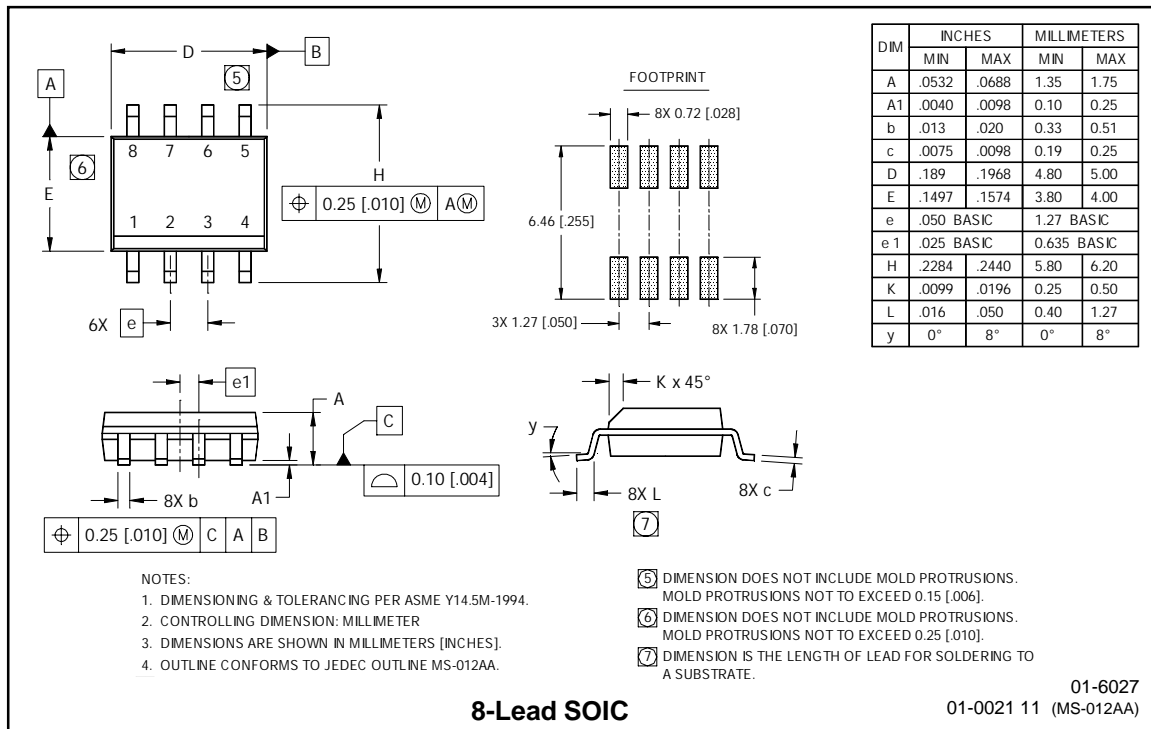
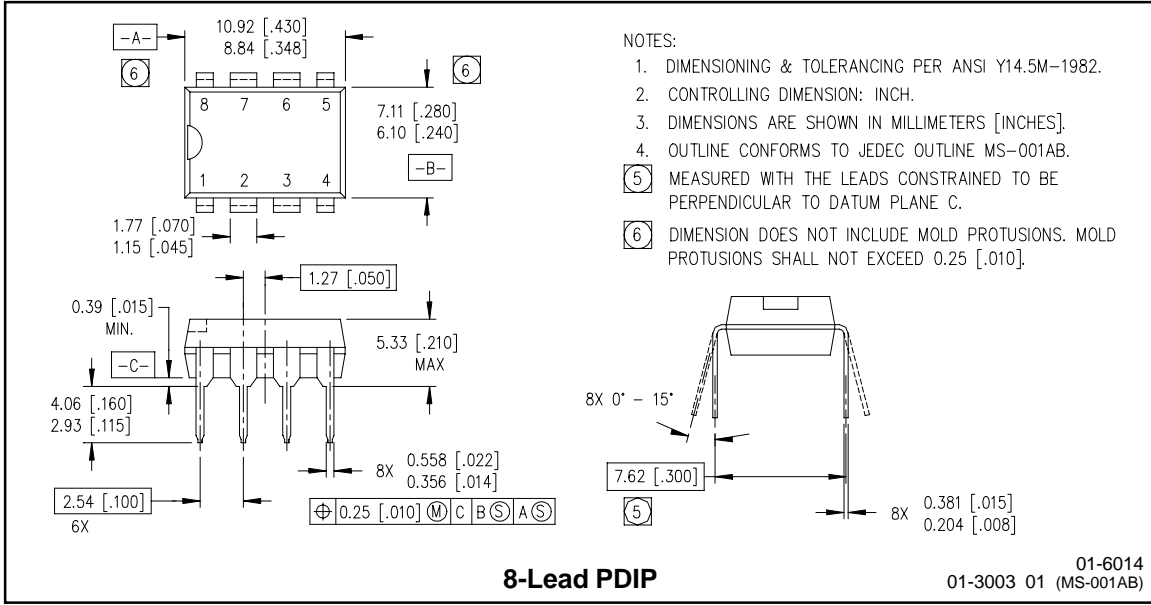


Figure 3. Deadtime Waveform Definitions

International  
**IR** Rectifier

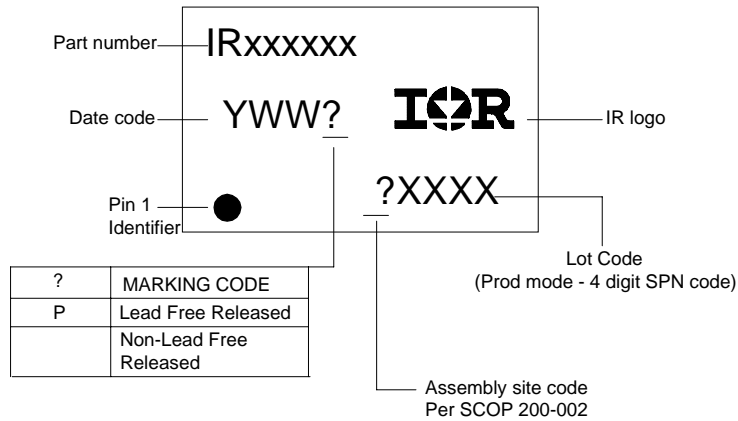
IR WORLD HEADQUARTERS: 233 Kansas Street, El Segundo, California 90245 Tel: (310) 252-7105  
Data and specifications subject to change without notice. 3/19/2003

## Case outlines



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## LEADFREE PART MARKING INFORMATION



## ORDER INFORMATION

### Basic Part (Non-Lead Free)

8-Lead PDIP IR2308 order IR2308  
8-Lead SOIC IR2308S order IR2308S

### Leadfree Part

8-Lead PDIP R2308 not available  
8-Lead SOIC IR2308S order IR2308SPbF